

## Description

The PSMTO11R4H uses split gate trench technology to provide excellent  $R_{DS(ON)}$  low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

### MOSFET Product Summary

$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
100	4.1@ $V_{GS} = 10V$	165

## Feature

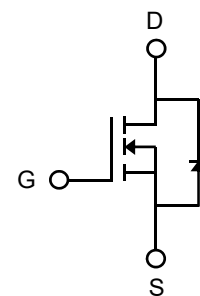
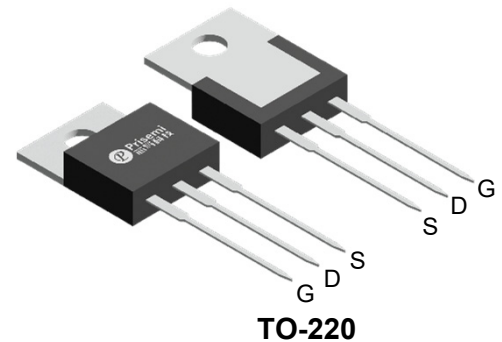
- Low  $R_{DS(ON)}$  - Ensures On-State Losses are Minimized
- Excellent  $Q_{gd} \times R_{DS(ON)}$  Product(FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% UIS (Avalanche) Rated
- Lead-Free Finish ; RoHS Compliant
- Halogen and Antimony Free. "Green" Device

## Applications

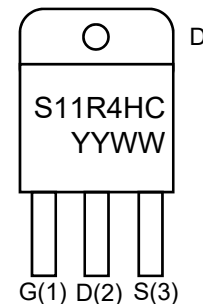
- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers

## Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous <sup>1)</sup>	$I_D$	$T_C=25^\circ C$	165
		$T_C=100^\circ C$	105
Pulsed Drain Current <sup>2)</sup>	$I_{DM}$	660	A
Total Power Dissipation <sup>3)</sup>	$P_D$	235.8	W
Avalanche Current <sup>4)</sup>	$I_{AS}$	123	A
Avalanche Energy <sup>4)</sup>	$E_{AS}$	766	mJ
Thermal Resistance , Junction-case <sup>5)</sup>	$R_{\theta JC}$	0.53	$^\circ C/W$
Thermal Resistance Junction-to-Ambient <sup>6)</sup>	$R_{\theta JA}$	50.3	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$



**Circuit Diagram**



**Marking (Top View)**

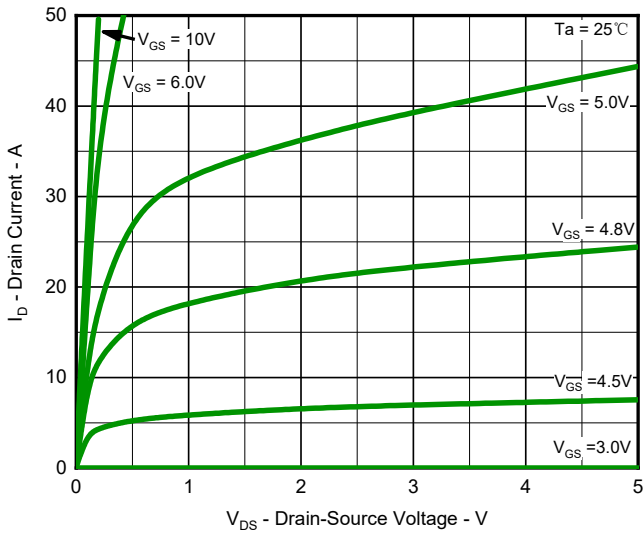
## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	113	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100V, V_{GS} = 0V$	-	-	1.0	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	3.2	4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 50A$	-	4.1	4.5	m $\Omega$
<b>Dynamic Characteristics<sup>7)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 50V, V_{GS} = 0V,$ $f = 1.0MHz$	-	5988	-	pF
Output Capacitance	$C_{oss}$		-	809	-	
Reverse Transfer Capacitance	$C_{rss}$		-	28	-	
<b>Switching Characteristics<sup>7)</sup></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 50V, V_{GS} = 10V,$ $R_G = 10\Omega, I_D = 15A$	-	44	-	ns
Turn-on Rise Time	$t_r$		-	70	-	
Turn-Off Delay Time	$t_{d(off)}$		-	125	-	
Turn-Off Fall Time	$t_f$		-	70	-	
Total Gate Charge	$Q_g$	$V_{DS} = 50V, V_{GS} = 10V,$ $I_D = 50A$	-	101	-	nC
Gate-Source Charge	$Q_{gs}$		-	30	-	
Gate-Drain Charge	$Q_{gd}$		-	27	-	
Gate Resistance	$R_g$	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	-	2.1	-	$\Omega$
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 1A$	-	0.7	1.4	V

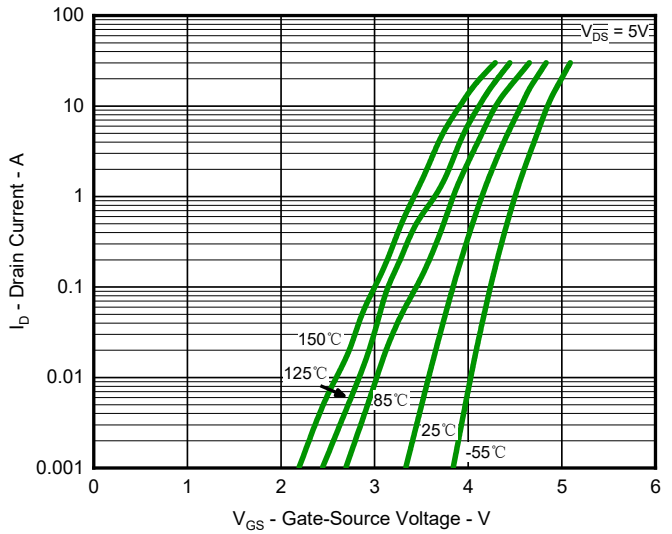
## Notes:

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature( $T_{J\_Max}=175^\circ C$ ).
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. This single-pulse measurement was taken under the following condition [ $L=100\mu H, V_{GS}=10V, V_{DS}=100V$ ]while it's value is limited by  $T_{J\_Max}=175^\circ C$
5. Device mounted on infinite heatsink
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Guaranteed by design, not subject to production

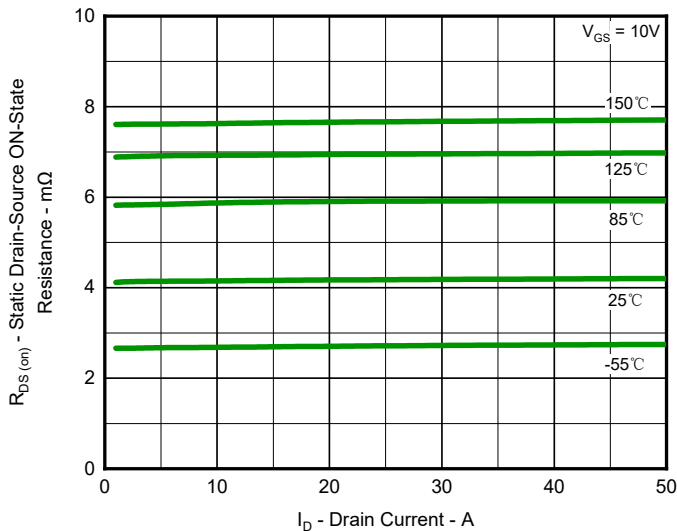
## Typical Characteristics



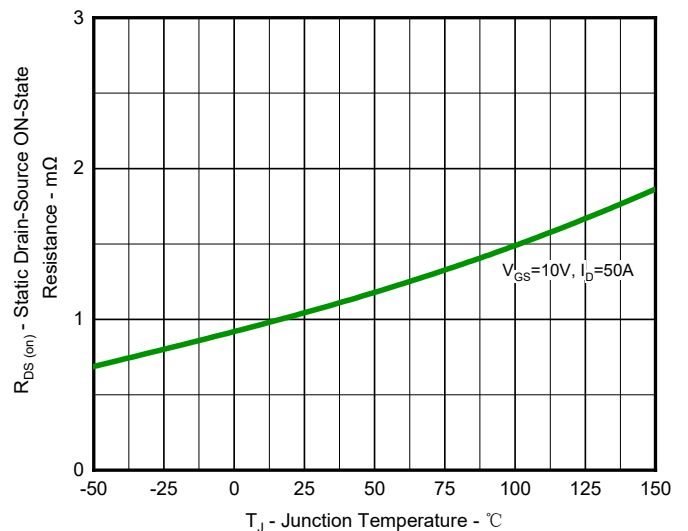
**Fig.1 Output Characteristics**



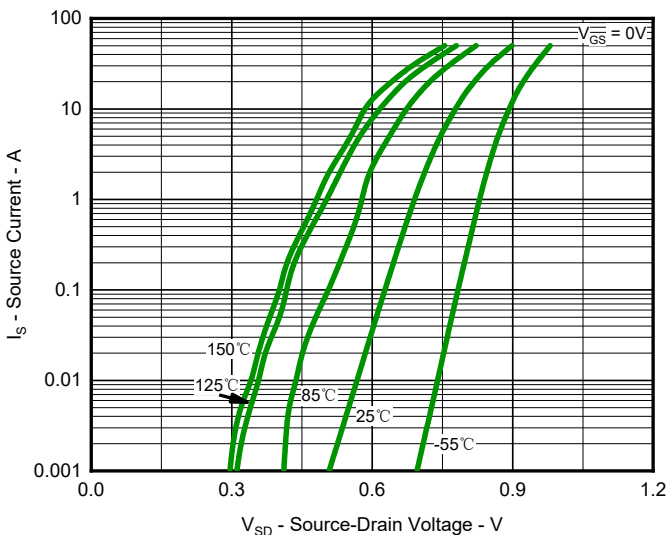
**Fig.2 Typical Transfer Characteristic**



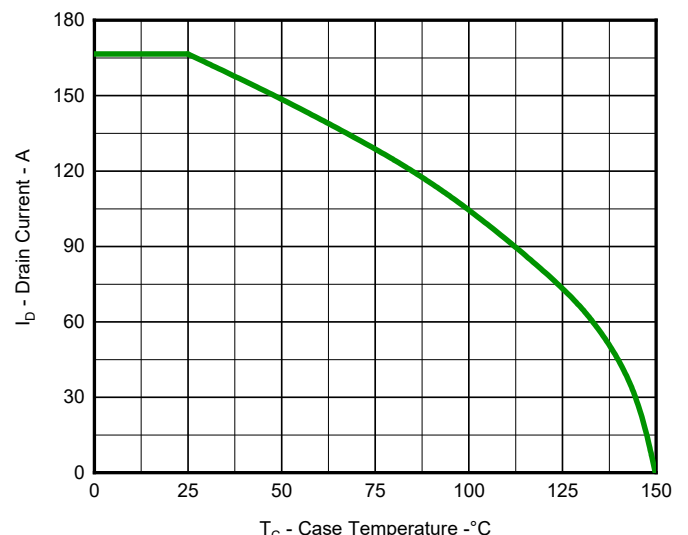
**Fig.3 Typical On-Resistance vs Drain Current and Temperature**



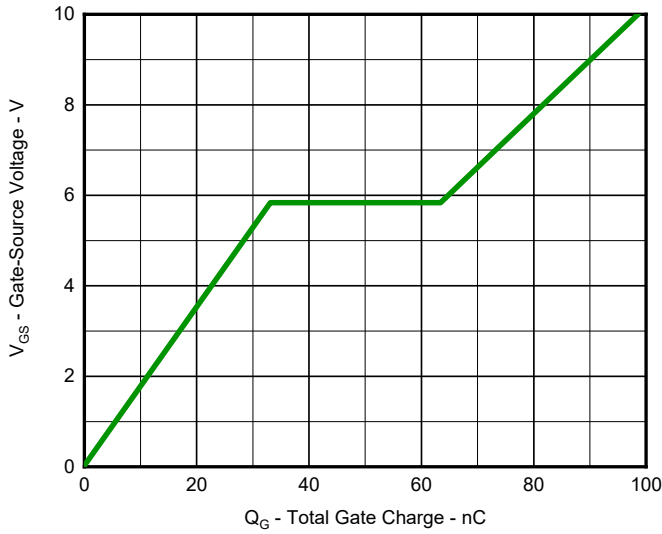
**Fig.4 On-Resistance Variation with Temperature**



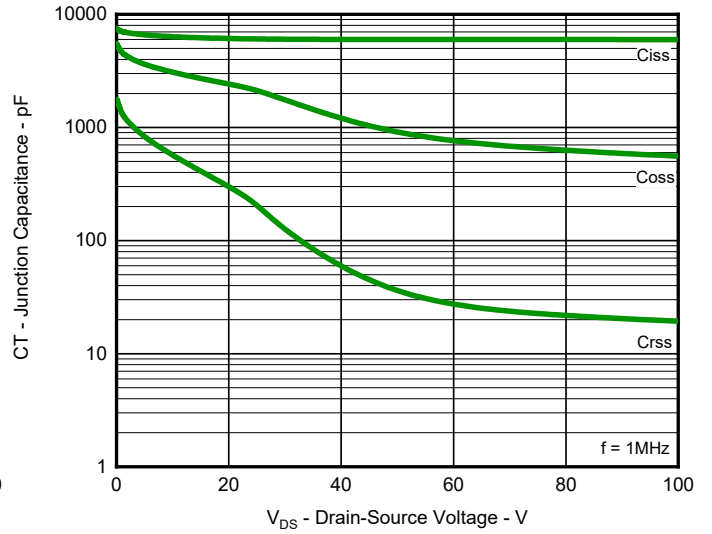
**Fig.5 Diode Forward Voltage vs. Current**



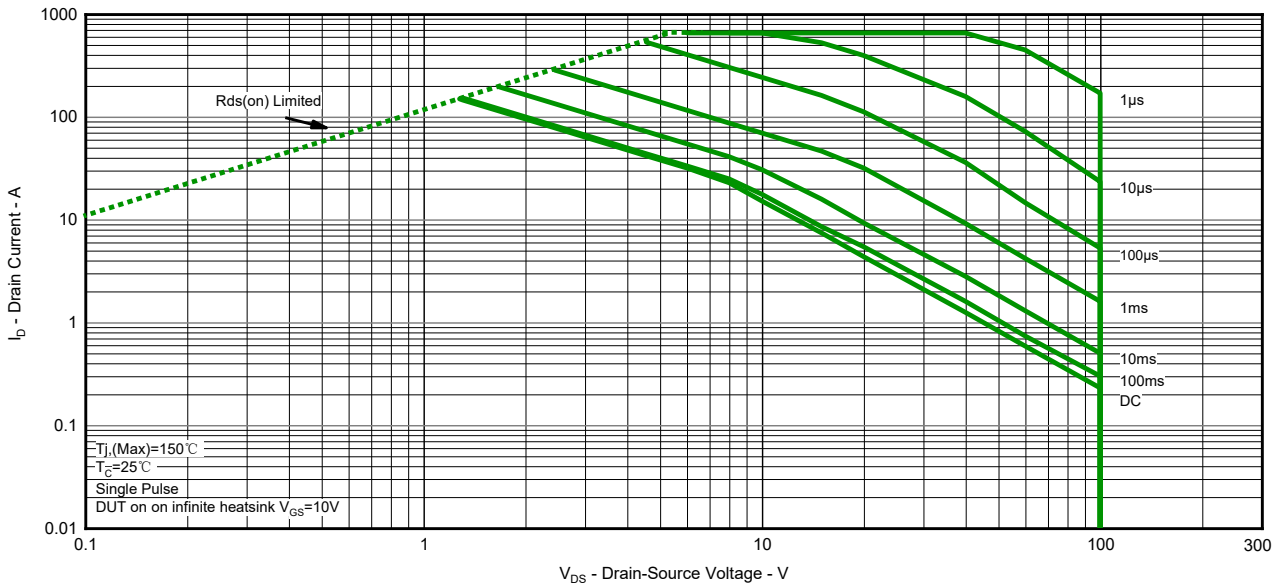
**Fig.6 Maximum Drain Current vs. Case Temperature**



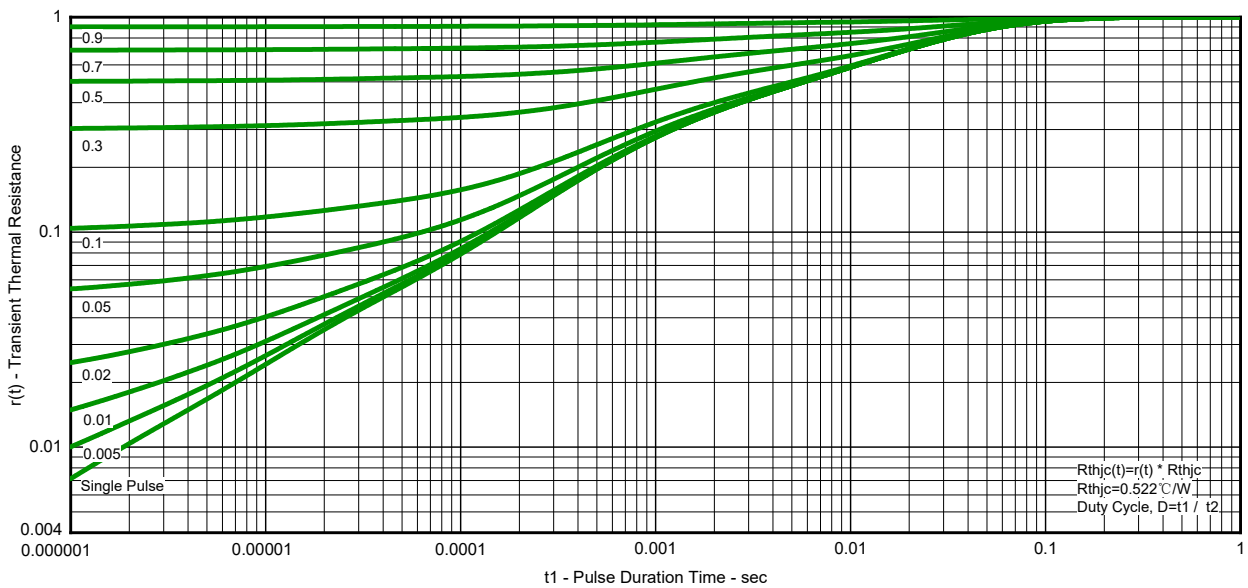
**Fig.7 Gate Charge Characteristics**



**Fig.8 Typical Junction Capacitance**

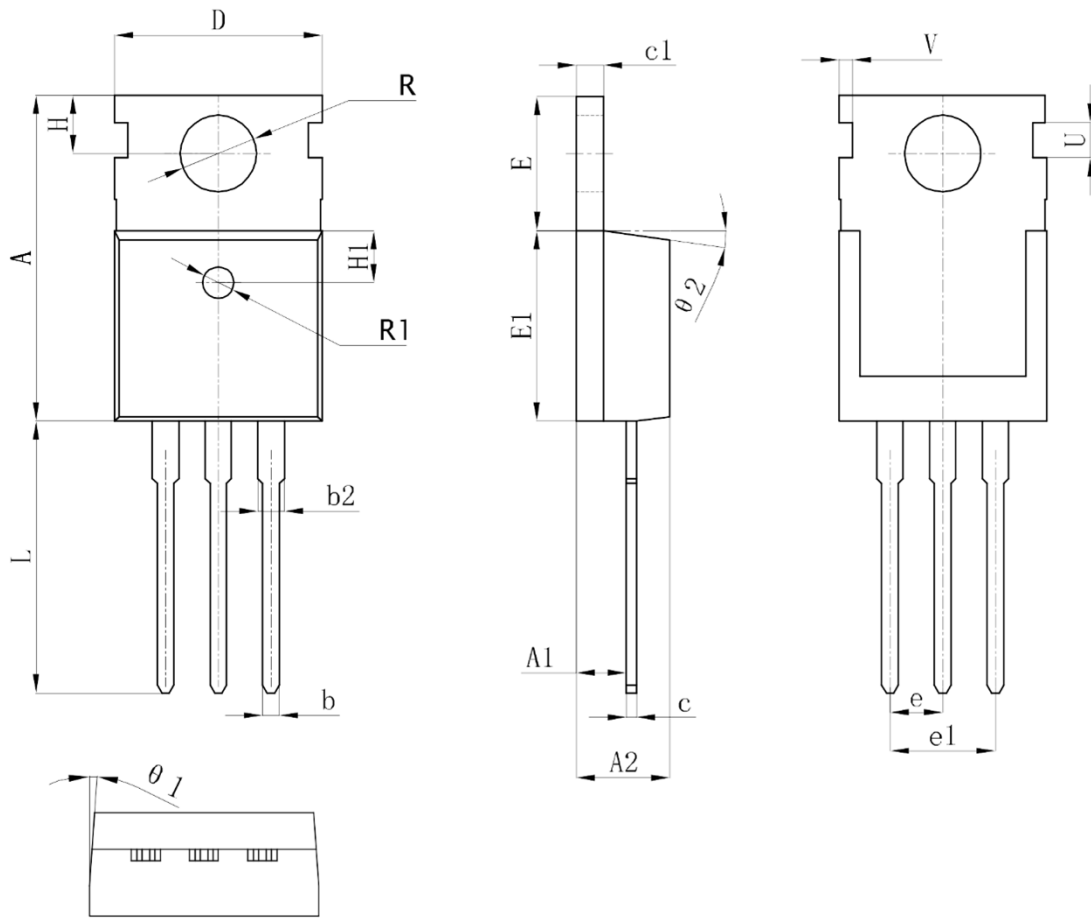


**Fig.9 Safe Operation Area**




**Fig.10 Transient Thermal Resistance**

## Product dimension (TO-220)



Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	15.40	15.80	0.606	0.622	e1	4.84	5.32	0.191	0.209
A1	2.35	2.50	0.093	0.098	H	2.73	2.87	0.107	0.113
A2	4.40	4.70	0.173	0.185	H1	2.40	2.60	0.094	0.102
b	0.70	0.90	0.028	0.035	L	13.02	13.72	0.513	0.540
b2	1.18	1.44	0.046	0.057	R	3.50	3.63	0.138	0.143
c	0.48	0.56	0.019	0.022	R1	1.40	1.60	0.055	0.063
c1	1.29	1.32	0.051	0.052	U	1.65	1.85	0.065	0.073
D	9.80	10.20	0.386	0.402	V	0.58	0.78	0.023	0.031
E	6.40	6.60	0.252	0.260	theta 1	2°	3°	2°	3°
E1	9.00	9.20	0.354	0.362	theta 2	6.5°	7.5°	6.5°	7.5°
e	2.42	2.66	0.095	0.105					


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